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台舟电子

PUMH2

Dual Digital Transistors (NPN+NPN)

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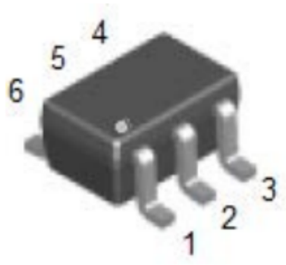
Features

- Two PUMH2 chips in a package
- Mounting possible with SOT-363 automatic mounting machines
- Transistor elements are independent,eliminating interference
- Mouting cost and area be cut in half

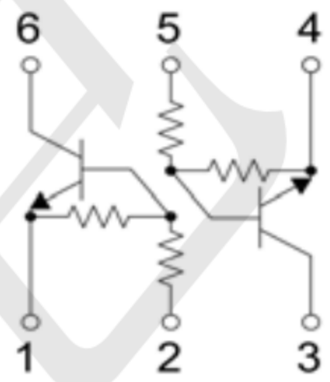
Ordering Information

Shipping Qty:3000 /7inch Tape& Reel



SOT363

Circuit Diagram



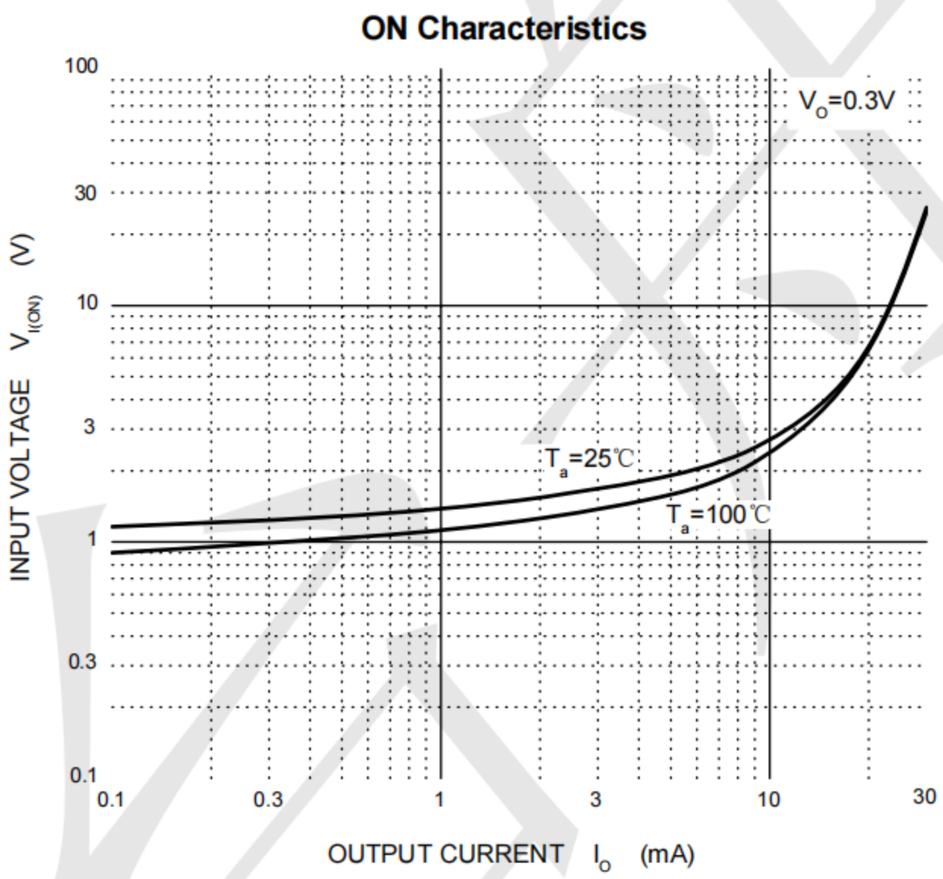
Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

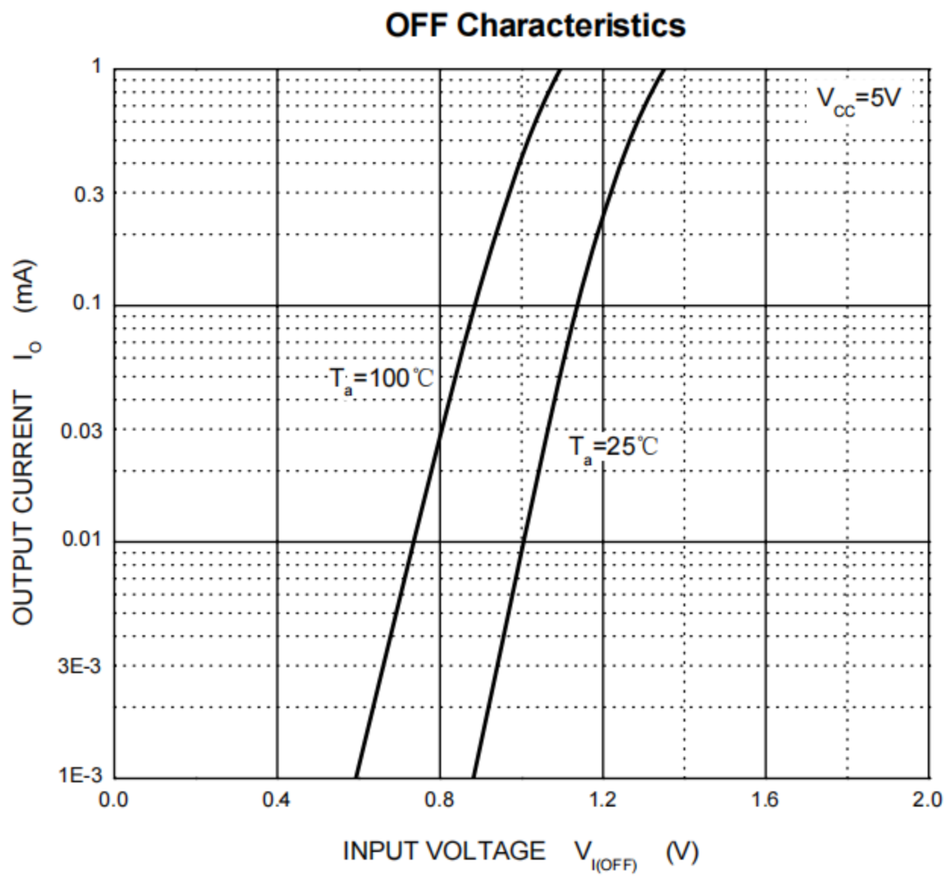
Symbol	Parameter	Value	Units
V_{CC}	Supply Voltage	50	V
V_i	Input voltage	-10 to +40	V
$I_{C(MAX)}$	Output current	100	mA
P_D	Power dissipation	150	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Input turn-on voltage	$V_{i(on)}$	V_{CC}=0.3V, I_O=2mA			3	V
Input cut-off voltage	$V_{i(off)}$	V_{CC}=5V, I_O=100μA	0.5			V
Output voltage	$V_{o(on)}$	I_O=10mA, I_i=0.5mA			0.3	V
Input cut-off current	I_i	V_i=5V			0.18	mA
Output cut-off current	$I_{O(off)}$	V_{CC}=50V, V_i=0			0.5	μA
DC current gain	G_i	V_O=5V, I_O=5mA	68			
Transition frequency	f_T	V_O=10V, I_O=5mA, f=100MHz		250		MHz
Input resistance	R_1		32.9		61.1	KΩ
Resistance ratio	R_2/R_1		0.8		1.2	

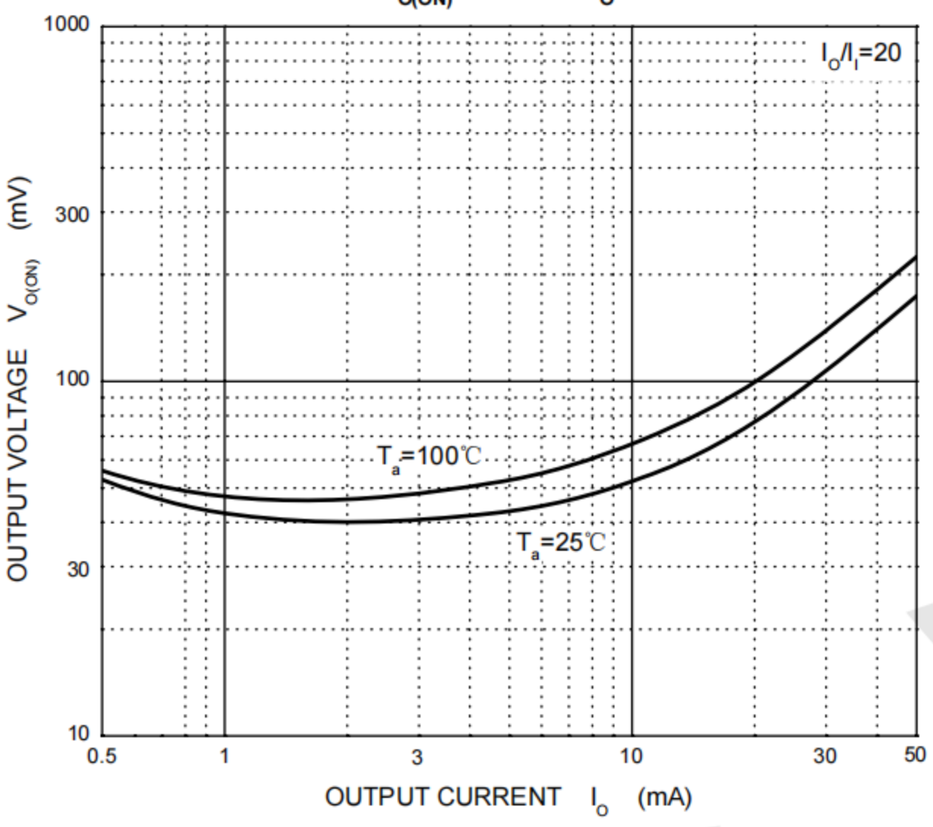
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



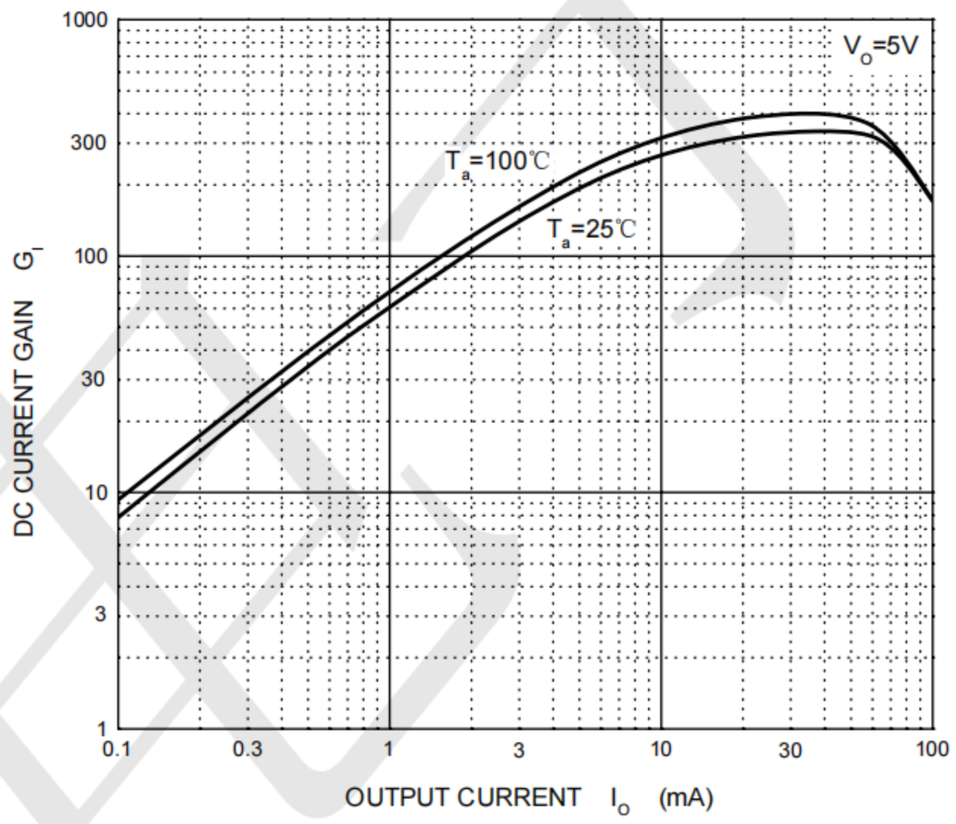


Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

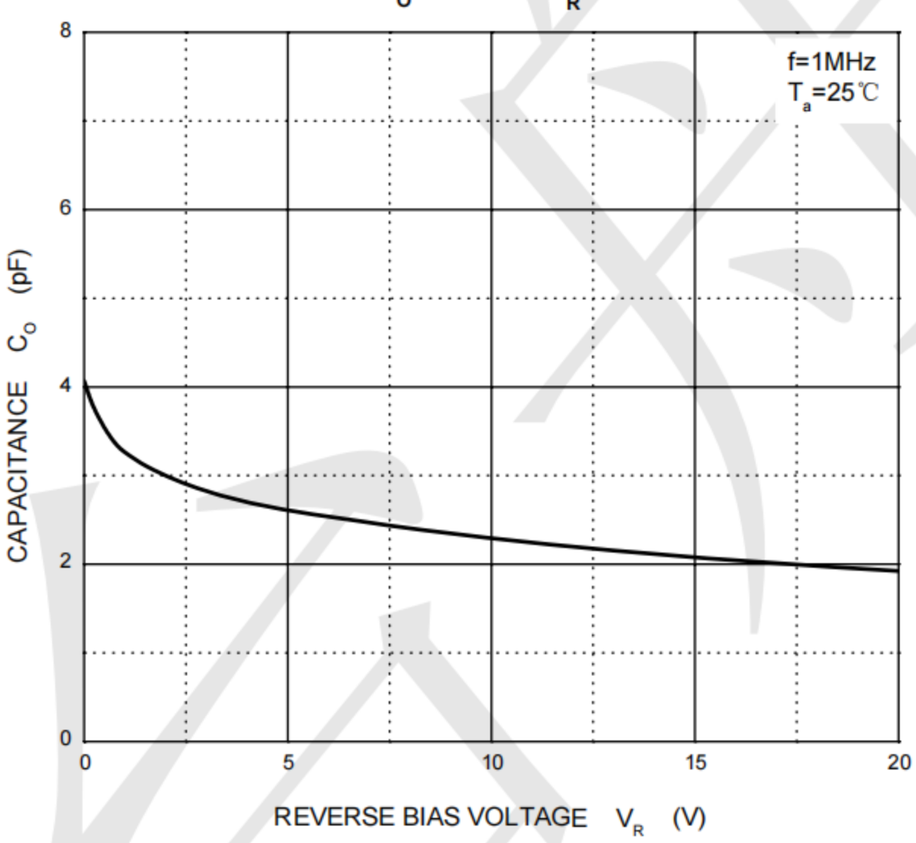
$V_{O(ON)}$ — I_O



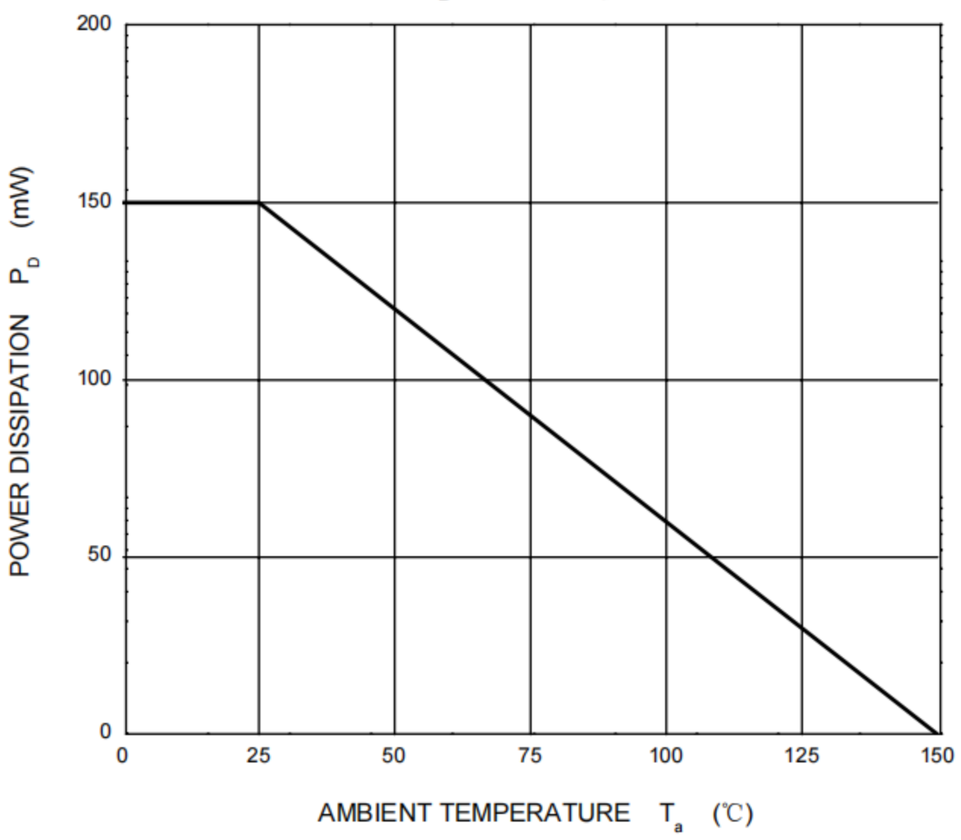
G_I — I_O



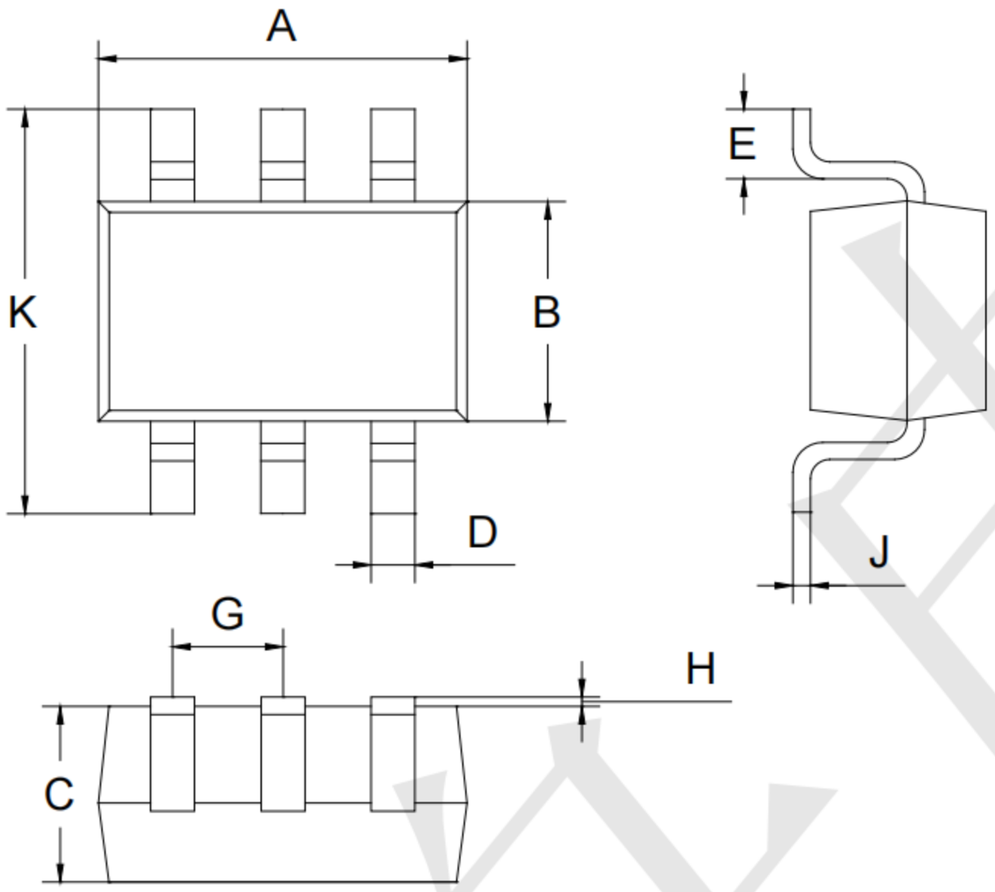
C_O — V_R



P_D — T_a



Outline Drawing - SOT363 (unit: mm)



SOT-363		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout-SOT363 (unit: mm)